



**THE DATASHEET OF  
MBR16100CT**



# MBR16100CTG

## Switch-mode Power Rectifier

### Features and Benefits

- Low Forward Voltage
- Low Power Loss/High Efficiency
- High Surge Capacity
- 175°C Operating Junction Temperature
- Low Stored Charge Majority Carrier Conduction
- 16 A Total (8.0 A Per Diode Leg)
- This Device is Pb-Free and is RoHS Compliant\*

### Applications

- Power Supply – Output Rectification
- Power Management
- Instrumentation

### Mechanical Characteristics

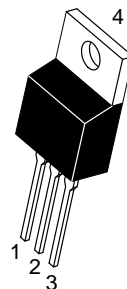
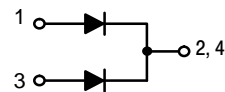
- Case: Epoxy, Molded
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- ESD Rating: Human Body Model = 3B  
Machine Model = C



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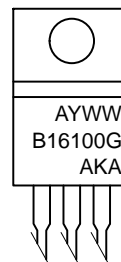
[www.onsemi.com](http://www.onsemi.com)

## SCHOTTKY BARRIER RECTIFIER 16 AMPERES, 100 VOLTS



TO-220  
CASE 221A  
STYLE 6

### MARKING DIAGRAM



A = Assembly Location  
Y = Year  
WW = Work Week  
B16100 = Device Code  
G = Pb-Free Package  
AKA = Diode Polarity

### ORDERING INFORMATION

Device	Package	Shipping
MBR16100CTG	TO-220 (Pb-Free)	50 Units/Rail

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# MBR16100CTG

## MAXIMUM RATINGS (Per Diode Leg)

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	100	V
Average Rectified Forward Current ( $T_C = 166^\circ\text{C}$ ) Per Diode Per Device	$I_{F(AV)}$	8.0 16	A
Peak Repetitive Forward Current (Square Wave, 20 kHz) $T_C = 165^\circ\text{C}$	$I_{FRM}$	16	A
Non-repetitive Peak Surge Current (Surge applied at rated load conditions half-wave, single phase, 60 Hz)	$I_{FSM}$	150	A
Peak Repetitive Reverse Surge Current (2.0 $\mu\text{s}$ , 1.0 kHz)	$I_{RRM}$	0.5	A
Operating Junction Temperature (Note 1)	$T_J$	-65 to +175	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-65 to +175	$^\circ\text{C}$
Voltage Rate of Change (Rated $V_R$ )	$dv/dt$	10,000	V/ $\mu\text{s}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction-to-Ambient:  $dP_D/dT_J < 1/R_{\theta JA}$ .

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Thermal Resistance, Junction-to-Case (Min. Pad) Junction-to-Ambient (Min. Pad)	$R_{\theta JC}$ $R_{\theta JA}$	2.0 60	$^\circ\text{C/W}$

## ELECTRICAL CHARACTERISTICS (Per Diode Leg)

Characteristic	Symbol	Min	Typical	Max	Unit
Maximum Instantaneous Forward Voltage (Note 2) ( $i_F = 8.0\text{ A}$ , $T_J = 125^\circ\text{C}$ ) ( $i_F = 8.0\text{ A}$ , $T_J = 25^\circ\text{C}$ ) ( $i_F = 16\text{ A}$ , $T_J = 125^\circ\text{C}$ ) ( $i_F = 16\text{ A}$ , $T_J = 25^\circ\text{C}$ )	$V_F$	-	0.56 0.68 0.67 0.79	0.60 0.74 0.69 0.84	V
Maximum Instantaneous Reverse Current (Note 2) (Rated dc Voltage, $T_J = 125^\circ\text{C}$ ) (Rated dc Voltage, $T_J = 25^\circ\text{C}$ )	$i_R$	-	0.95 0.0013	5.0 0.1	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle  $\leq 2\%$ .

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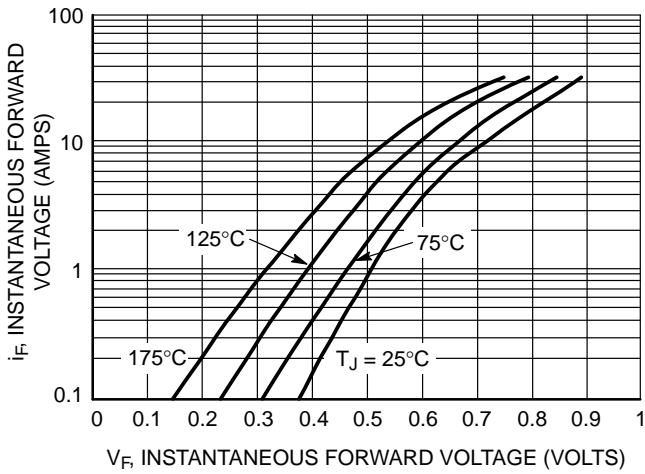


Figure 1. Typical Forward Voltage Per Diode

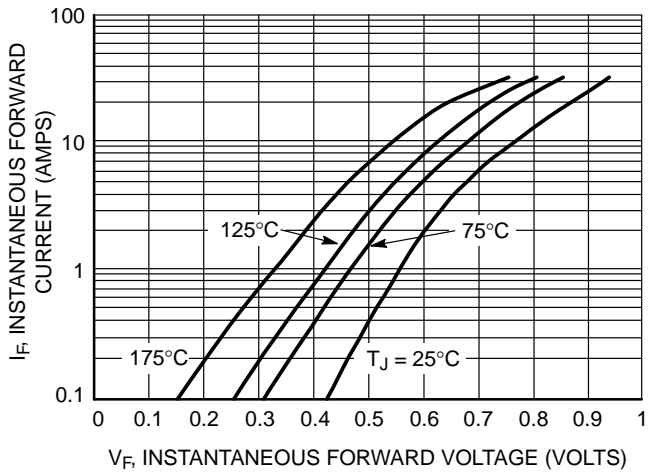


Figure 2. Maximum Forward Voltage Per Diode

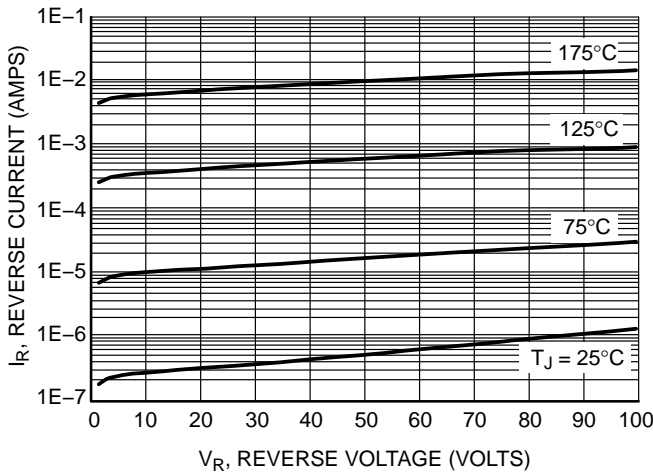


Figure 3. Typical Reverse Current Per Diode

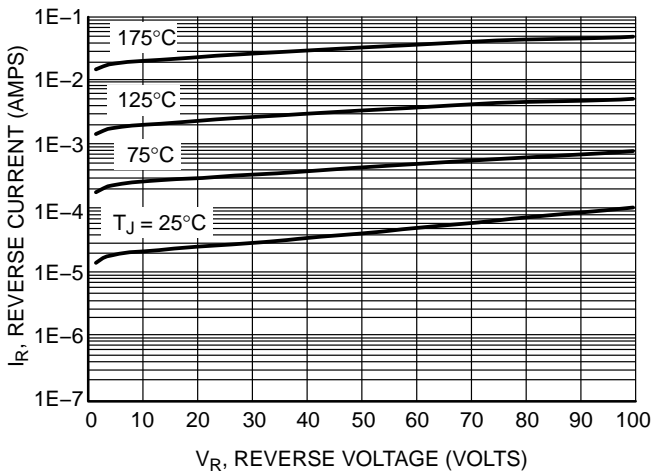


Figure 4. Typical Capacitance Per Diode

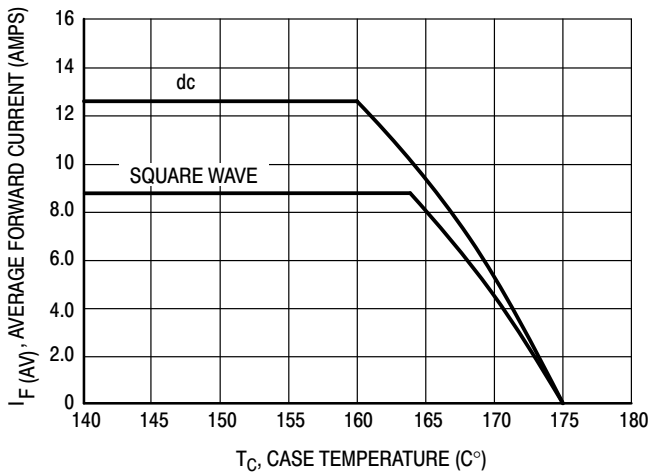


Figure 5. Current Derating, Case Per Leg

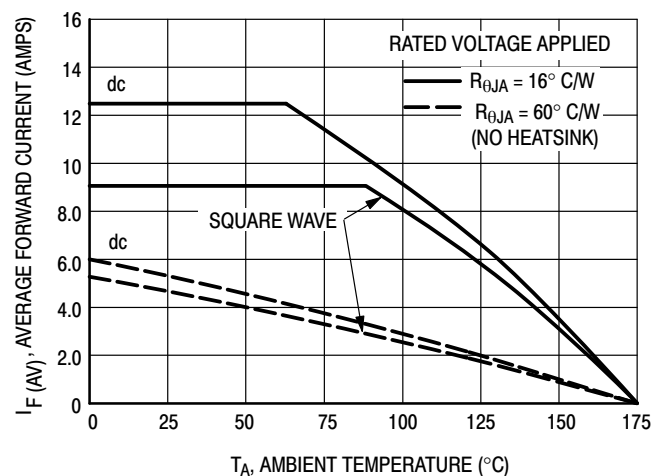


Figure 6. Current Derating, Ambient Per Leg

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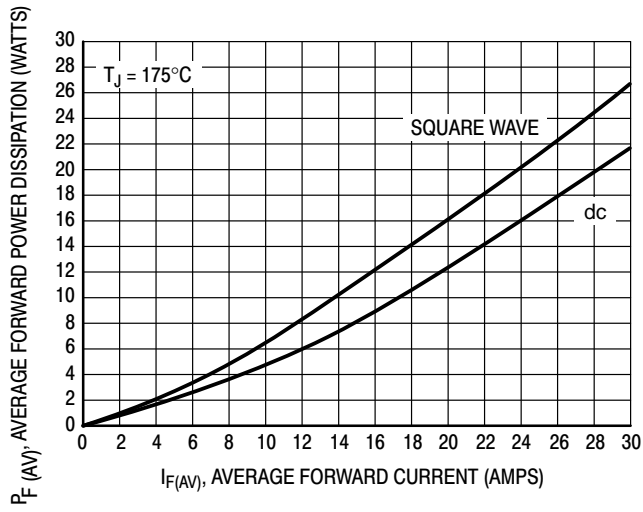


Figure 7. Forward Power Dissipation

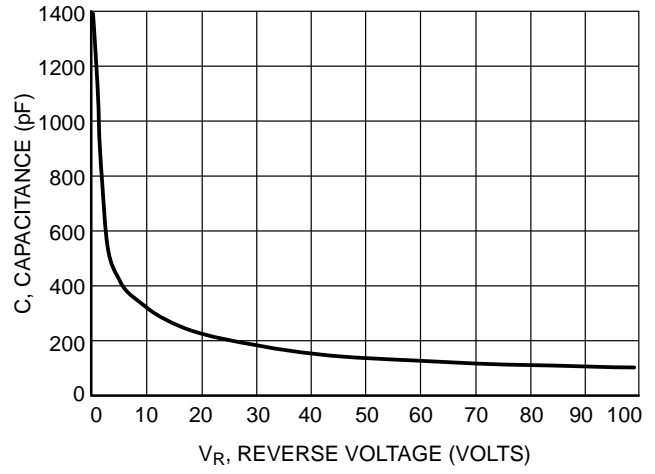


Figure 8. Typical Capacitance Per Diode

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